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KA1M0565R/KA1H0565R

Fairchild Power Switch(FPS)

Features

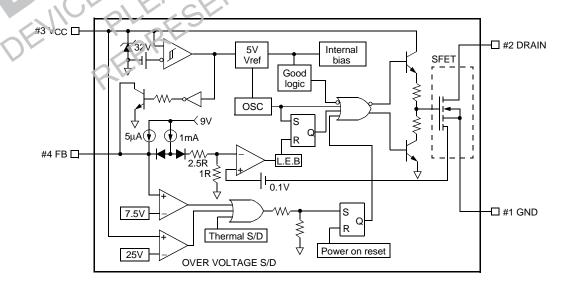
- Precision fixed operating frequency
- KA1M0565R (67KHz),KA1H0565R (100KHz)
- Pulse by pulse over current limiting
- · Over load protection
- Over voltage protection (Min. 23V)
- Internal thermal shutdown function
- Under voltage lockout
- Internal high voltage sense FET
- · Auto restart

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit, compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a for vard converter.



Internal Block Diagram



Absolute Maximum Ratings

Single pulsed avalanche energy (3) Continuous drain current (T _C =25°C) ID 5.0 Continuous drain current (T _C =100°C) ID 3.5 Maximum Supply voltage VCC,MAX Input voltage range VFB -0.3 to VSD Total power dissipation	meter	Symbol	Value	Unit
Gate-source (GND) voltage VGS	mum Drain voltage ⁽¹⁾	V _D ,MAX	650	V
Drain current pulsed (2) IDM 20 Single pulsed avalanche energy (3) EAS 230 Continuous drain current (Tc=25°C) ID 5.0 Continuous drain current (Tc=100°C) ID 3.5 Maximum Supply voltage Vcc,MAX 30 Input voltage range VFB -0.3 to VsD Total power dissipation PD 140 Derating 1.11 V Operating ambient temperature TA -25 to +85 Storage temperature TSTG 55 to + 50 Notes:	n Gate voltage (R _{GS} =1MΩ)	VDGR	650	V
Single pulsed avalanche energy (3) EAS 230 Continuous drain current (T _C =25°C) ID 5.0 Continuous drain current (T _C =100°C) ID 3.5 Maximum Supply voltage VCC,MAX 30 Input voltage range VFB -0.3 to VSD Total power dissipation PD 140 Derating 111 Operating ambient temperature TA -25 to +85 Storage temperature TSTG 55 to +50 Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximum junction temperature 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	-source (GND) voltage	Vgs	±30	V
Continuous drain current (Tc=25°C)	r current pulsed ⁽²⁾	IDM	20	ADC
Continuous drain current (TC=100°C) ID 3.5 Maximum Supply voltage VCC,MAX 30 Input voltage range VFB -0.3 to VSD PD 140 Derating 1.11 V Operating ambient temperature TA -25 to +85 Storage temperature TSTG 55 to +150 Iotes: . Tj=25°C to 150°C Repetitive rating: Pulse width limited by maximum junction temperature . L=30mH, VpD=50V, RG= 27Ω, starting Tj=25°C	e pulsed avalanche energy (3)	EAS	230	mJ
Maximum Supply voltage VCC,MAX 30 Input voltage range VFB -0.3 to VSD Total power dissipation PD 140 Derating 1,11 1 Operating ambient temperature TA -25 to +8c Storage temperature TSTG 55 to + 150 Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximum junction temperature 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	inuous drain current (T _C =25°C)	ID	5.0	ADC
Input voltage range	inuous drain current (Tc=100°C)	ID	3.5	ADC
Total power dissipation PD 140 Derating 1.11 Operating ambient temperature TA -25 to +8s Storage temperature TSTG 55 to +50 Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximum junction temperature 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	mum Supply voltage	VCC,MAX	30	V
Total power dissipation Derating Derating 1.11 Operating ambient temperature TA -25 to +85 Storage temperature TSTG -55 to + 50 Notes: Tj=25°C to 150°C Repetitive rating: Pulse width limited by maximum junction temperature L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	voltage range	VFB	-0.3 to VSD	V
Derating 11 1 1 1 1 1 1 1 1	nower dissipation	PD	140	W
Storage temperature TSTG 55 to + 50 Notes: Tj=25°C to 150°C Repetitive rating: Pulse width limited by maximum junction temperature L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	power dissipation	Derating	1,11	W/°C
Notes: I. Tj=25°C to 150°C I. Repetitive rating: Pulse width limited by maximum junction temperature I. L=30mH, Vpp=50V, Rg= 27Ω, starting Tj=25°C	ating ambient temperature	TA	-25 to +85	°C
Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximum junction temperature 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	age temperature	TSTG	-55 to +150	°C
DE" DEE	B0mH, V _{DD} =50V, R _G = 27Ω, starting Tj=25	°C ONNE	DED ORN	ATIO

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

	Symbol	Condition	Min.	Тур.	Max.	Uni
Drain source breakdown voltage	BVDSS	VGS=0V, ID=50μA	650	-	-	V
Zero gate voltage drain current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
Zero gate voltage drain current	פפטי	V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μΑ
Static drain source on resistance (note)	RDS(ON)	Vgs=10V, ID=2.5A	-	1.76	2.2	Ω
Forward transconductance (note)	gfs	V _{DS} =50V, I _D =2.5A	2.5		-	S
Input capacitance	Ciss	.,,	-	1457	-	,
Output capacitance	Coss	VGS=0V, VDS=25V, f=1MHz		130	7 - ,	φF
Reverse transfer capacitance	Crss	1-11VII 12	-	38.8		
Turn on delay time	td(on)	V _{DD} =0.5BV _{DSS} , I _D =5.0A	-		60	
Rise time	tr	(MOSFET switching		10	150	
Turn off delay time	td(off)	time are essentially independent of	0	-	300	nS
Fall time	tf	operating temperature)	77	lo-	130	
Total gate charge	0.00	VGS=10V, ID=5.0A,	-6	SIL	56	
	Qg	VDS=0.5B VDSS (MOSFET	100	.1		
(gate-source+gate-drain) Gate source charge	Qgs	switching time are	0,- "	10.3	-	n(
(gate-source+gate-drain)	Qgs	switching time are essentially independent of	OR	10.3	-	nC

Electrical Characteristics (CONTROL part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit		
UVLO SECTION								
Start threshold voltage	VSTART	-	14	15	16	V		
Stop threshold voltage	VSTOP	After turn on	9	10	11	V		
OSCILLATOR SECTION				•	•	•		
Initial accuracy	Fosc	KA1M0565R	61	67	73	kHz		
		KA1H0565R	90	100	110	KHZ		
Frequency change with temperature (2)	ΔΕ/ΔΤ	–25°C ≤ Ta ≤ +85°C	-	±5	±10	%		
Maximum duty avala	D	KA1M0565R	74	77	30	. 60		
Maximum duty cycle	Dmax	KA1H0565R	64	67	70	%		
FEEDBACK SECTION								
Feedback source current	IFB	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA		
Shutdown Feedback voltage	VsD		6.9	7.5	8.1	V		
Shutdown delay current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VsD	4.0	5.0	6.0	μΑ		
REFERENCE SECTION								
Output voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V		
Temperature Stability (1)(2)	Vref/△T	-25°C ≤ Ta ≤ +85°C	0.7	0.3	0.6	mV/°C		
CURRENT LIMIT (SELF-PROTECTION) SECTION								
Peak Current Limit	lover	Max inductor current	3.03	3.5	3.92	Α		
PROTECTION SECTION		10, 4 4 10,		•	•	•		
Thermal shutdown temperature (Tj) (1)	TSD	10 -2 "	140	160	-	°C		
Over voltage protection voltage	VOVP	(K) 50,	23	25	28	V		
TOTAL DEVICE SECTION								
Start Up current	START	VCC=14V	0.1	0.3	0.4	mA		
Operating supply current (control part only)	lor	Ta=25°C	6	12	18	mA		
VCC zener voltage	Vz	ICC=20mA	30	32.5	35	V		

Note:

These parameters, although guaranteed, are not 100% tested in production
 These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

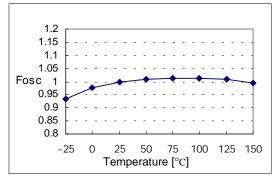


Figure 1. Operating Frequency

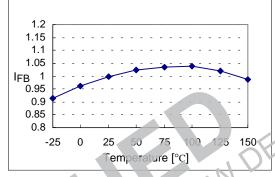


Figure 2. Feedback Source Current

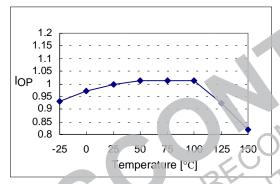


Figure 3. Operating Supply Current

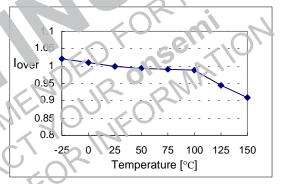


Figure 4. Peak Current Limit

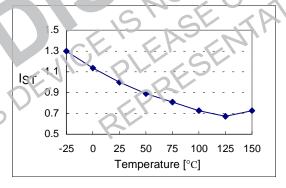


Figure 5. Start up Current

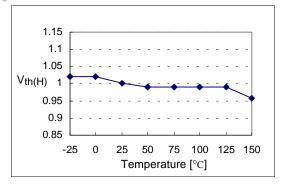


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

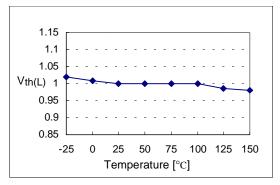


Figure 7. Stop Threshold Voltage

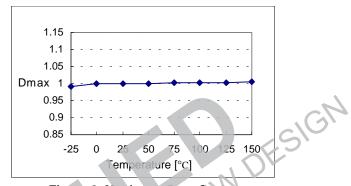


Figure 8. Maximum Duty Cycle

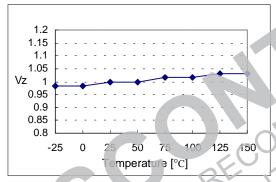


Figure 9. Vcc Zener Voltage

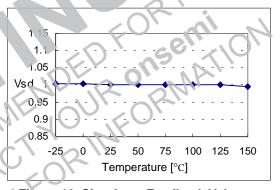


Figure 10. Shutdown Feedback Voltage

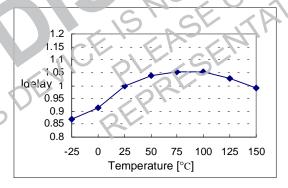


Figure 11. Shutdown Delay Current

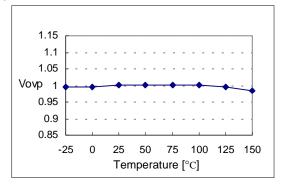


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic grahps are normalized at Ta=25°C)

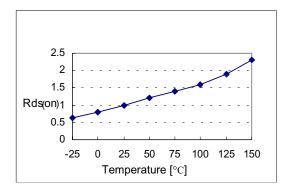
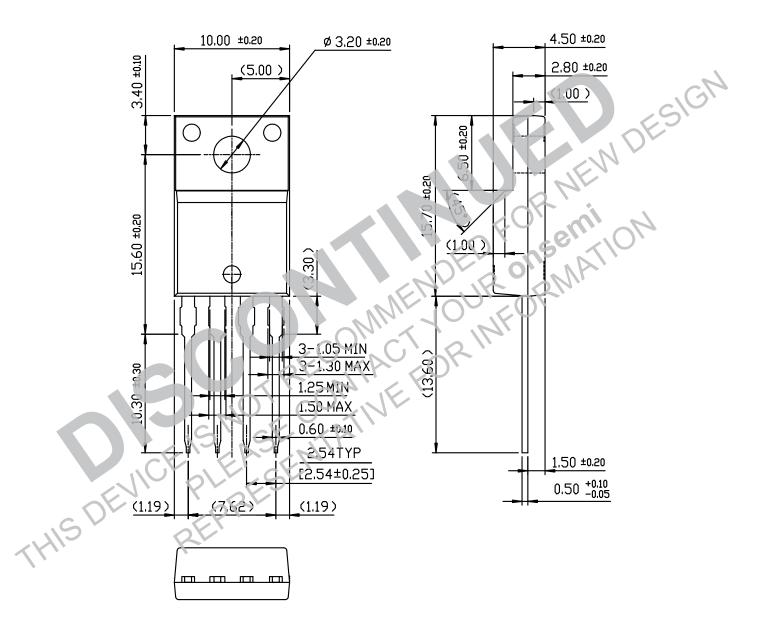


Figure 13. Static Drain-Source on Resistance

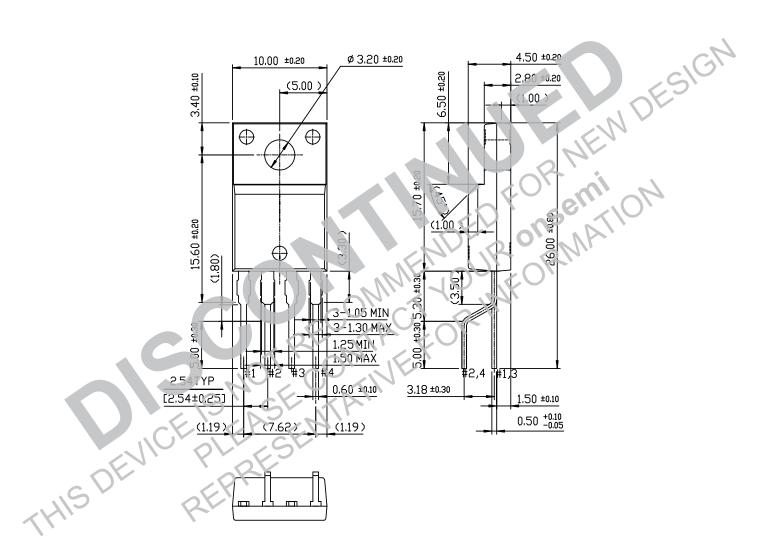
Package Dimensions

TO-220F-4L



Package Dimensions (Continued)

TO-220F-4L(Forming)



Ordering Information

Product Number	Package	Rating	Fosc
KA1M0565R-TU	TO-220F-4L	650V, 5A	67kHz
KA1M0565R-YDTU	TO-220F-4L(Forming)	650 V, 5A	07 KHZ
KA1H0565R-TU	TO-220F-4L	650V, 5A	100kHz
KA1H0565R-YDTU	TO-220F-4L(Forming)	030 V, 3A	TOURNZ

TU : Non Forming Type YDTU : Forming Type



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